transphorm

TP90H050WS (Preliminary)

900V Cascode GaN FET in TO-247 (source tab)

Description

The TP90H050WS, 900V, 50mΩ gallium nitride (GaN) FETs is a normally-off device, combining a low voltage silicon MOSFET with industry-leading threshold voltage for increased robustness and noise immunity, and the market's most reliable depletion mode GaN FET.

Transphorm GaN offers better efficiency over silicon, through lower gate charge, lower cross-over losses, and smaller reverse recovery charge.

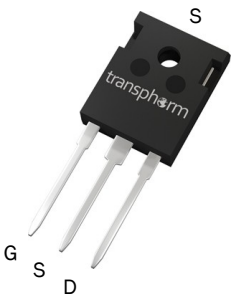
Related Literature

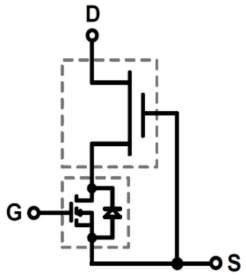
- AN0009: Recommended External Circuitry for GaN FETs
- AN0003: Printed Circuit Board Layout and Probing

Ordering Information

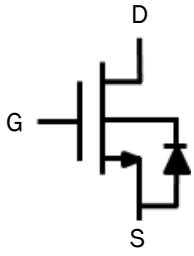
Part Number	Package	Package Configuration
TP90H050WS	3 Lead TO-247	Common Source

TP90H050WS
TO-247
(top view)





Cascode Device Structure



Cascode Schematic Symbol

Features

- JEDEC-qualified GaN technology
- Robust design, defined by
  — Lifetime intrinsic testing
  — Wide gate safety margin
  — Lower Qrr over silicon
- Reduced crossover loss
- Compatible with commonly-used gate drivers
- RoHS compliant and Halogen-free packaging

Benefits

- Enables AC-DC bridgeless totem-pole PFC designs—Increased power density
  — Reduced system size and weight
  — Overall lower system cost
- Achieves increased efficiency in both hard- and soft-switched topologies
- Easy to drive

Applications

- Renewable energy
- Industrial
- Telecom and datacom
- Servo motors

Key Specifications	
V_{DS} (V) min	900
V_{TDS} (V) max	1000
$R_{DS(on)}$ (mΩ) max*	60
Q_{rr} (nC) typ	150
Qg (nC) typ	16

* Dynamic $R_{(on)}$

Transphorm China
+86-13501775977
HZ021@QQ.COM

Absolute Maximum Ratings (T_C=25°C unless otherwise stated)

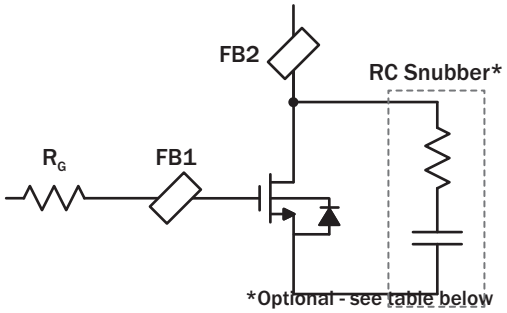
Symbol	Parameter		Limit Value	Unit
$I_{D25°C}$	Continuous drain current @T_C=25°C [a]		34	A
$I_{D100°C}$	Continuous drain current @T_C=100°C [a]		22	A
I_{DM}	Pulsed drain current (pulse width: 10μs)		150	A
V_{DSS}	Drain to source voltage		900	V
V_{TDS}	Transient drain to source voltage [b]		1000	V
V_{GSS}	Gate to source voltage		±20	V
$P_{D25°C}$	Maximum power dissipation		119	W
T_C	Operating temperature	Case	-55 to +150	°C
T_J		Junction	-55 to +150	°C
T_S	Storage temperature		-55 to +150	°C
T_{CSOLD}	Soldering peak temperature [c]		260	°C

Thermal Resistance

Symbol	Parameter	Typical	Unit
$R_{\Theta JC}$	Junction-to-case	1.05	°C/W
$R_{\Theta JA}$	Junction-to-ambient	40	°C/W

Notes:
a. For high current operation, see application note AN0009
b. In off-state, spike duty cycle D<0.01, spike duration <1μs
c. For 10 sec., 1.6mm from the case

Circuit Configuration[a]



a. Recommended gate drive: (8V to 12V, 0V), R_G = 10Ω

Sustained oscillation can occur in switching applications using high speed GaN devices, but must be prevented for safe operation. By inserting a ferrite bead and/or an RC snubber with the recommended values below, Transphorm GaN FETs can operate in a hard-switching bridge up to their full-rated current even with a less-than-ideal PCB layout. See application note AN0009: Recommended External Circuitry for more information.

Ferrite Beads and Recommended RC Snubbers

Devices	Gate Ferrite Bead (FB1)	Drain Ferrite Bead (FB2)	RC Snubber Network
TP65H050WS	External FB (40 - 60 Ω) optional	8.5A (BLM21SN300SN1D) x 3 12A (BLM31SN500SZ1L) x 2	47pF/100pF + 7.5Ω

Electrical Parameters (T_j=25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
$V_{DSS-MAX}$	Maximum drain-source voltage	900	—	—	V	V_{GS}=0V
$V_{GS(th)}$	Gate threshold voltage [d]	3.4	3.9	4.4	V	V_{DS}=V_{GS}, I_D=0.7mA
$R_{DS(on)}$	Drain-source on-resistance [a]	—	50	63	mΩ	V_{GS}=10V, I_D=24A, T_J=25°C
	Drain-source on-resistance [a]	—	105	—		V_{GS}=10V, I_D=24A, T_J=150°C
I_{DSS}	Drain-to-source leakage current	—	4	40	μA	V_{DS}=650V, V_{GS}=0V, T_J=25°C
	Drain-to-source leakage current	—	15	—		V_{DS}=650V, V_{GS}=0V, T_J=150°C
I_{GSS}	Gate-to-source forward leakage current	—	—	100	nA	V_{GS}=20V
	Gate-to-source reverse leakage current	—	—	-100		V_{GS}=-20V
C_{ISS}	Input capacitance	—	960	—	pF	V_{GS}=0V, V_{DS}=600V, *f*=1MHz
C_{OSS}	Output capacitance	—	115	—		
C_{RSS}	Reverse transfer capacitance	—	—	—		
$C_{O(er)}$	Output capacitance, energy related [b]	—	—	—	pF	V_{GS}=0V, V_{DS}=0V to 600V
$C_{O(tr)}$	Output capacitance, time related [c]	—	233	—		
Q_g	Total gate charge	—	28	40	nC	V_{DS}=600V, V_{GS}=0V to 10V, I_D=24A
Q_{gs}	Gate-source charge	—	10	—		
Q_{gd}	Gate-drain charge	—	6	—		
$t_{d(on)}$	Turn-on delay	—	—	—	ns	V_{DS}=600V, V_{GS}=0V to 10V, I_D=24A, R_G=10Ω
t_r	Rise time	—	—	—		
$T_{d(off)}$	Turn-off delay	—	—	—		
t_f	Fall time	—	—	—		
Reverse Device Characteristics						
I_S	Reverse current	—	—	22	A	V_{GS}=0V, T_C=100°C ≤50% Duty Cycle
V_{SD}	Reverse voltage [a]	—	2.2	2.6	V	V_{GS}=0V, I_S=24A, T_J=25°C
		—	1.6	1.9		V_{GS}=0V, I_S=12A, T_J=25°C
t_{rr}	Reverse recovery time	—	30	—	ns	I_S=24A, V_{DD}=400V, di/dt=1000A/μs, T_J=25°C
Q_{rr}	Reverse recovery charge	—	150	—	nC	

Notes:
a. Dynamic value
b. Equivalent capacitance to give same stored energy from 0V to 400V
c. Equivalent capacitance to give same charging time from 0V to 400V
d. Recommended gate drive: (8V to 12V, 0V) R_G = 10Ω

Test Circuits and Waveforms

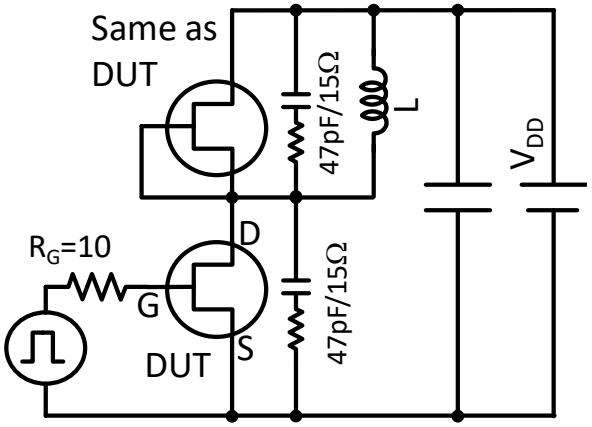


Figure 13. Switching Time Test Circuit
***See app note AN0009 for methods to ensure clean switching**

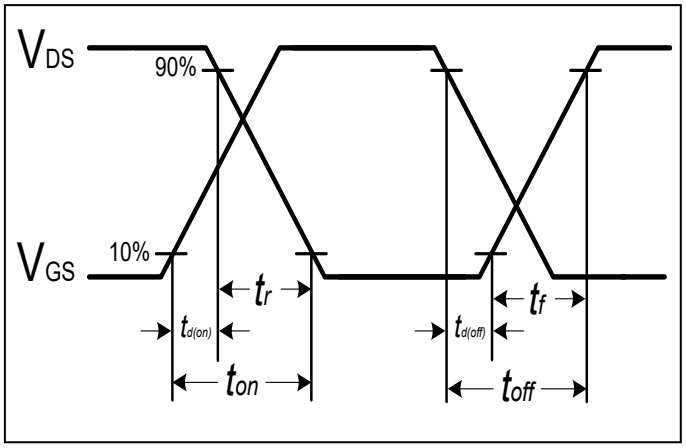


Figure 14. Switching Time Waveform

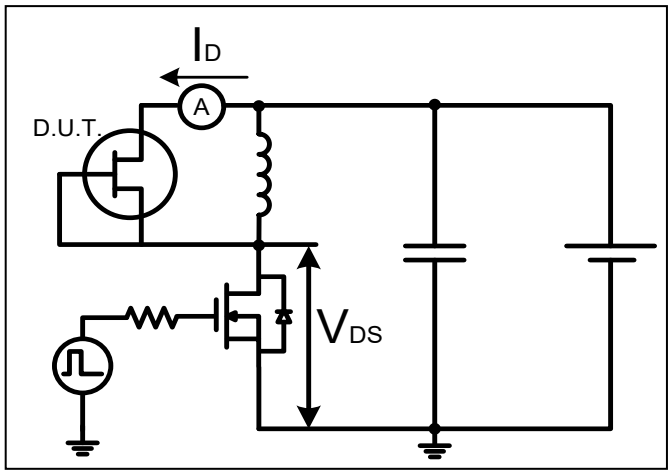


Figure 15. Test Circuit for Diode Characteristics

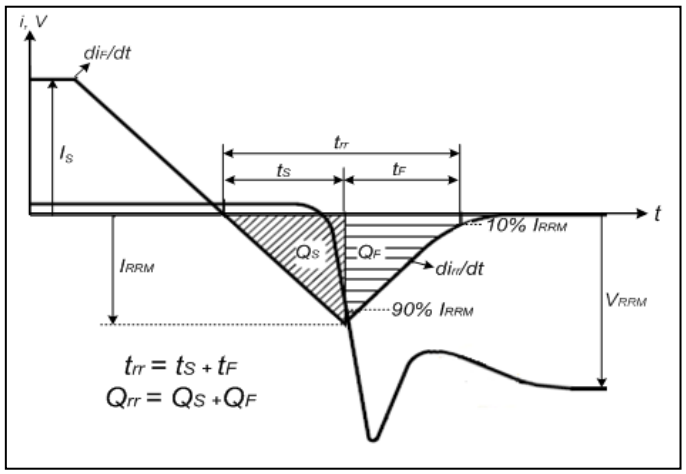


Figure 16. Diode Recovery Waveform

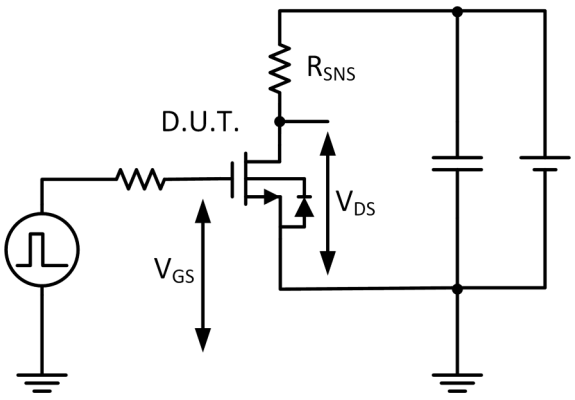


Figure 17. Test Circuit for Dynamic $R_{DS(on)}$

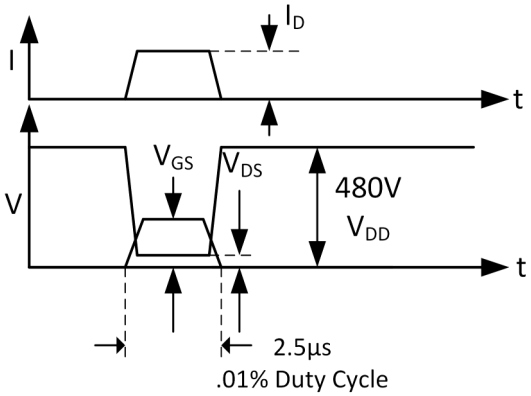
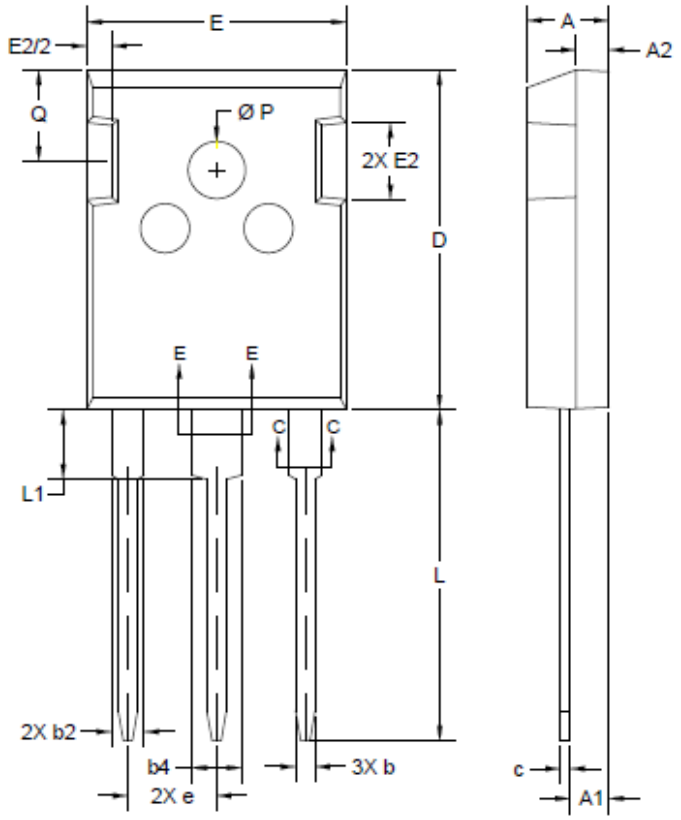


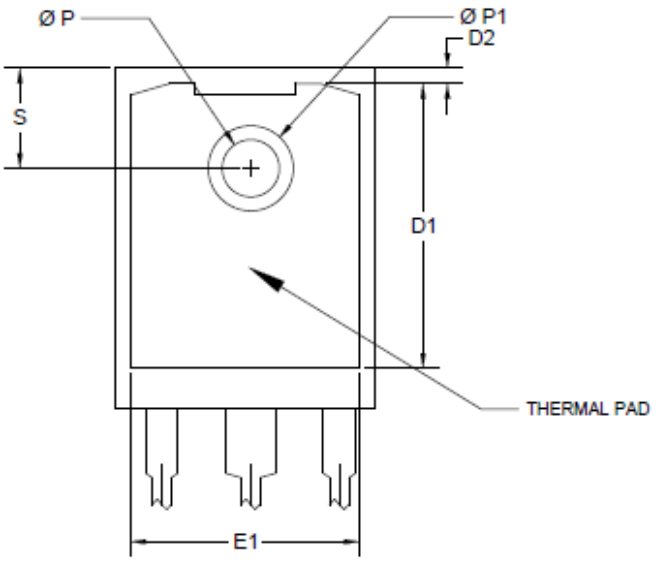
Figure 18. Dynamic $R_{DS(on)}$ Waveform

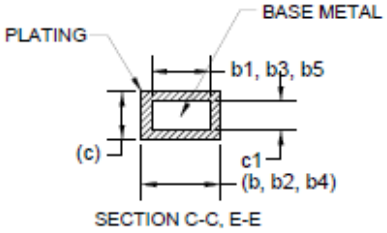
Mechanical

3 Lead TO-247 Package



SYMBOL	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.82	5.00	5.19	0.190	0.197	0.204
A1	2.20	2.39	2.57	0.087	0.094	0.101
A2	1.82	2.01	2.18	0.072	0.079	0.086
b	1.09	1.19	1.35	0.043	0.047	0.053
b1	1.09	-	1.30	0.043	-	0.051
b2	1.87	2.03	2.31	0.074	0.080	0.091
b3	1.87	-	2.27	0.074	-	0.089
b4	2.94	3.05	3.22	0.116	0.120	0.127
b5	2.94	-	3.18	0.116	-	0.125
c	0.50	0.58	0.68	0.020	0.023	0.027
c1	0.50	-	0.64	0.020	-	0.025
D	20.67	20.85	21.11	0.814	0.821	0.831
D1	17.20	-	17.63	0.677	-	0.694
D2	0.81	-	1.20	0.032	-	0.048
E	15.72	15.90	16.15	0.619	0.626	0.636
E1	13.79	-	14.25	0.543	-	0.561
E2	4.30	-	4.86	0.169	-	0.191
e	5.46 BSC			0.215 BSC		
L	19.55	19.94	20.38	0.770	0.785	0.802
L1	3.93	4.11	4.48	0.155	0.162	0.176
ØP	3.50	3.61	3.69	0.138	0.142	0.145
ØP1	7.08	7.19	7.32	0.279	0.283	0.288
Q	5.41	-	5.85	0.213	-	0.230
S	6.15 BSC			0.242 BSC		





SECTION C-C, E-E

NOTES:

1. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 MM (0.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
2. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS D1 & E1.
3. LEAD FINISH UNCONTROLLED IN L1.
4. OUTLINE CONFORMS TO JEDEC TO-247AD.

TO-247 3L			
transphorm			
SCALE: 1:1	SHEET 1/1	DRAWING NO. 200019	VER. 3

Design Considerations

The fast switching of GaN devices reduces current-voltage cross-over losses and enables high frequency operation while simultaneously achieving high efficiency. However, taking full advantage of the fast switching characteristics of GaN switches requires adherence to specific PCB layout guidelines and probing techniques.

Before evaluating Transphorm GaN devices, see application note Printed Circuit Board Layout and Probing for GaN Power Switches. The table below provides some practical rules that should be followed during the evaluation.

When Evaluating Transphorm GaN Devices:

DO	DO NOT
Minimize circuit inductance by keeping traces short, both in the drive and power loop	Twist the pins of TO-220 or TO-247 to accommodate GDS board layout
Minimize lead length of TO-220 and TO-247 package when mounting to the PCB	Use long traces in drive circuit, long lead length of the devices
Use shortest sense loop for probing; attach the probe and its ground connection directly to the test points	Use differential mode probe or probe ground clip with long wire
See AN0003: Printed Circuit Board Layout and Probing	

Application Notes

- AN0002: Characteristics of Transphorm GaN Power Switches
- AN0003: Printed Circuit Board Layout and Probing
- AN0004: Designing Hard-switched Bridges with GaN
- AN0008: Drain Voltage and Avalanche Ratings for GaN FETs
- AN0009: Recommended External Circuitry for GaN FETs

Revision History

Version	Date	Change(s)